## NSN 5961-00-112-3414

No Fiig: A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-112-3414 **Inclosure Material:** Metal or plastic **Overall Length:** 0.260 inches **Overall Height:** 0.080 inches **Overall Width:** 0.155 inches **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 60.0 breakdown voltage, collector-to-base, emitter open all transistor and 50.0 breakdown voltage, collector-to-emitter, base open all transistor and 5.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 30.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 350.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Test Data Document:** 94756-472-0961 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 6 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:**